

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	180	V
Collector-emitter voltage	V _{CEO}	160	V
Emitter-base voltage	V _{EB0}	6	V
Collector current-continuous	I _c	0.6	A
Collector Power Dissipation	P _c	625	mW
Junction and storage temperature	T _J , T _{stg}	- 5 5 t o + 1 5 0	°C

Collector-base breakdown voltage	V _{CB0}	I _c = 100 ìA, I _E = 0	180		V
Collector-emitter breakdown voltage *	V _{CEO}	I _c = 1.0 mA, I _B = 0	160		V
Emitter-base breakdown voltage	V _{EB0}	I _E = 10 ìA, I _c = 0	6		V
Collector cutoff current	I _{CB0}	V _{CB} = 120 V, I _E = 0		50	nA
Emitter cutoff current	I _{EB0}	V _{EB} = 4.0 V, I _c = 0		50	nA
DC current gain *	h _{FE}	I _c = 1.0 mA, V _{CE} = 5 V	80		
		I _c = 10 mA, V _{CE} = 5 V	80	250	
		I _c = 50 mA, V _{CE} = 5 V	30		
Collector-emitter saturation voltage *	V _{CE(sat)}	I _c = 10 mA, I _B = 1 mA		0.15	V
		I _c = 50 mA, I _B = 5mA		0.2	
Base-emitter saturation voltage *	V _{BE(sat)}	I _c = 10 mA, I _B = 1 mA		1.0	V
		I _c = 50 mA, I _B = 5 mA		1.0	
Transiston frequency	f _t	V _{CE} =10V, I _c =10mA, f=100MHz	100	300	MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		6	pF
Input capacitance	C _{ib}	V _{BE} =0.5V, I _c =0, f=1MHz		20	pF
Noise figure	NF	V _{CE} =5V, I _c =0.25mA, f=10Hz to 15.7KHz, R _s =1k _Ω			

* Pulse Test: Pulse Width = 300 μs, Duty Cycle=2.0%.